

Bias Resistor Transistor

PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

LDTA144VET1G

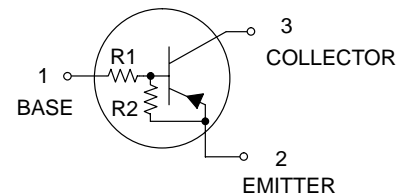
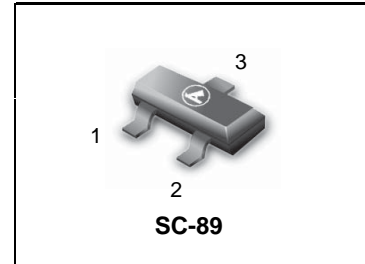
- **Applications**
Inverter, Interface, Driver

- **Features**
 - 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
 - 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
 - 3) Only the on/off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.

● **Absolute maximum ratings** (Ta=25°C)

| Parameter | Symbol | Limits | Unit |
|----------------------|----------------------|-------------|------|
| Supply voltage | V _{CC} | -50 | V |
| Input voltage | V _i | -40 to +15 | V |
| Output current | I _o | -30 | mA |
| | I _{c(Max.)} | -100 | |
| Power dissipation | P _d | 200 | mW |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |



DEVICE MARKING AND RESISTOR VALUES

| Device | Marking | R1 (K) | R2 (K) | Shipping |
|--------------|---------|--------|--------|------------------|
| LDTA144VET1G | L9 | 47 | 10 | 3000/Tape & Reel |
| LDTA144VET3G | L9 | 47 | 10 | 8000/Tape & Reel |

● **Electrical characteristics** (Ta=25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|----------------------|--------------------------------|------|------|-------|------|---|
| Input voltage | V _{I(off)} | - | - | -1 | V | V _{CC} = -5V , I _o = -100μA |
| | V _{I(on)} | -6 | - | - | | V _o = -0.3V , I _o = -2mA |
| Output voltage | V _{O(on)} | - | -0.1 | -0.3 | V | I _o = -10mA , I _i = -0.5mA |
| Input current | I _i | - | - | -0.16 | mA | V _i = -5V |
| Output current | I _{O(off)} | - | - | -0.5 | μA | V _{CC} = -50V , V _i =0V |
| DC current gain | G _i | 33 | - | - | - | I _o = -5mA , V _o = -5V |
| Input resistance | R ₁ | 32.9 | 47 | 61.1 | kΩ | - |
| Resistance ratio | R ₂ /R ₁ | 0.17 | 0.21 | 0.26 | - | - |
| Transition frequency | f _r | - | 250 | - | MHz | V _{CE} = -10V , I _E =5mA , f=100MHz * |

* Transition frequency of the device.

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● **Electrical characteristic curves**

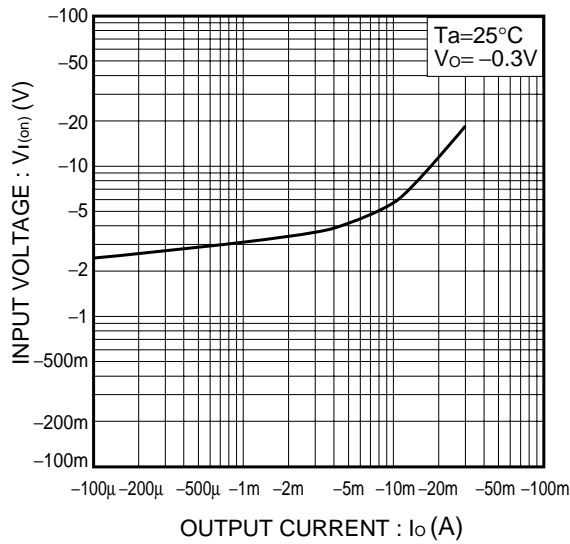


Fig.1 Input voltage vs. Output current (ON characteristics)

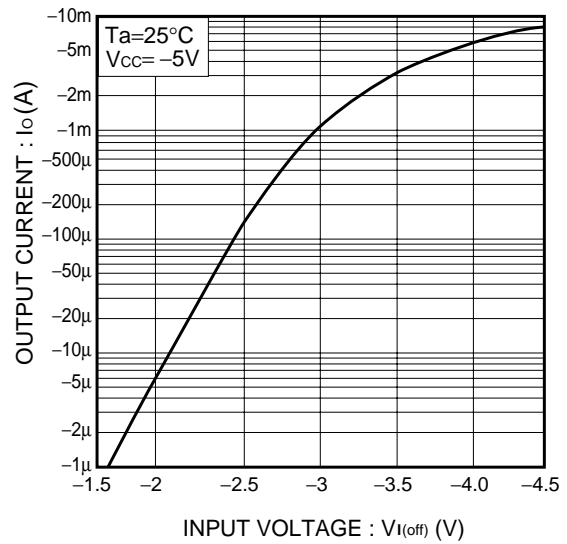


Fig.2 Output current vs. Input voltage (OFF characteristics)

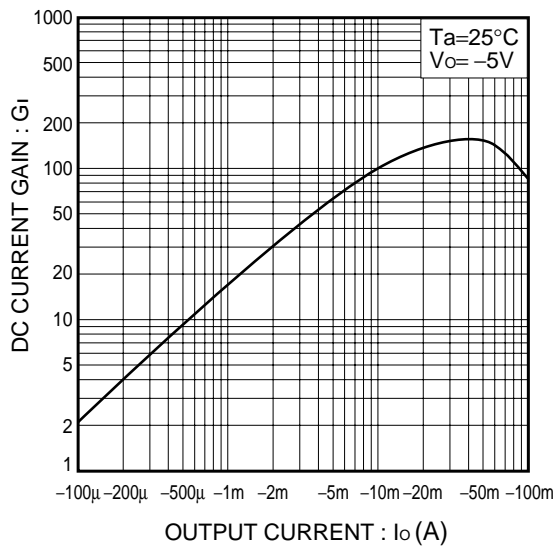


Fig.3 DC current gain vs. Output current characteristics

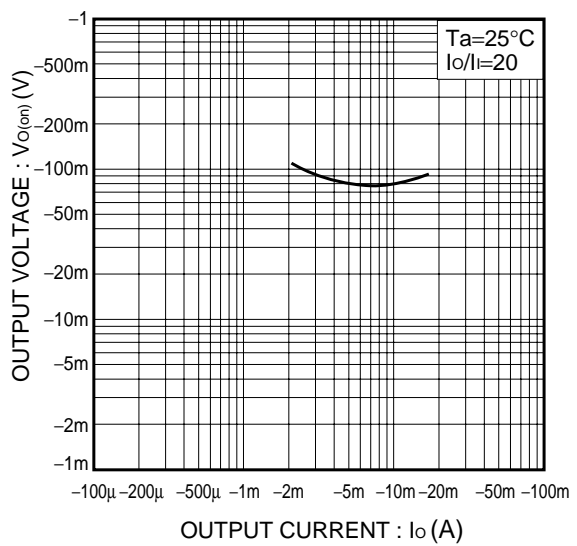
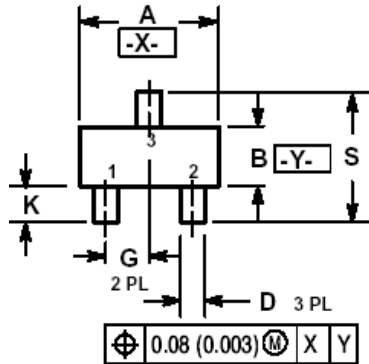
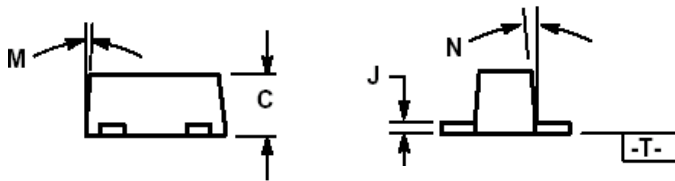


Fig.4 Output voltage vs. Output current characteristics

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.



| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|-----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 1.50 | 1.60 | 1.70 | 0.059 | 0.063 | 0.067 |
| B | 0.75 | 0.85 | 0.95 | 0.030 | 0.034 | 0.040 |
| C | 0.60 | 0.70 | 0.80 | 0.024 | 0.028 | 0.031 |
| D | 0.23 | 0.28 | 0.33 | 0.009 | 0.011 | 0.013 |
| G | 0.50 BSC | | | 0.020 BSC | | |
| H | 0.53 REF | | | 0.021 REF | | |
| J | 0.10 | 0.15 | 0.20 | 0.004 | 0.006 | 0.008 |
| K | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 |
| L | 1.10 REF | | | 0.043 REF | | |
| M | --- | --- | 10 ° | --- | --- | 10 ° |
| N | --- | --- | 10 ° | --- | --- | 10 ° |
| S | 1.50 | 1.60 | 1.70 | 0.059 | 0.063 | 0.067 |

